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# FDMS7700S

## Dual N-Channel PowerTrench<sup>®</sup> MOSFET

N-Channel: 30 V, 30 A, 7.5 mΩ N-Channel: 30 V, 40 A, 2.4 mΩ

### Features

Q1: N-Channel

- Max  $r_{DS(on)}$  = 7.5 mΩ at  $V_{GS} = 10$  V,  $I_D = 12$  A
- Max  $r_{DS(on)}$  = 12 mΩ at  $V_{GS} = 4.5$  V,  $I_D = 10$  A

Q2: N-Channel

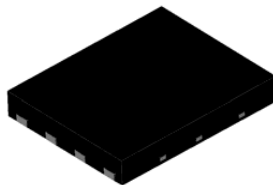
- Max  $r_{DS(on)}$  = 2.4 mΩ at  $V_{GS} = 10$  V,  $I_D = 20$  A
- Max  $r_{DS(on)}$  = 2.9 mΩ at  $V_{GS} = 4.5$  V,  $I_D = 18$  A
- RoHS Compliant

### General Description

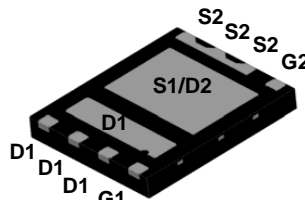
This device includes two specialized N-Channel MOSFETs in a dual MLP package. The switch node has been internally connected to enable easy placement and routing of synchronous buck converters. The control MOSFET (Q1) and synchronous SyncFET<sup>™</sup> (Q2) have been designed to provide optimal power efficiency.

### Applications

- Computing
- Communications
- General Purpose Point of Load
- Notebook VCORE

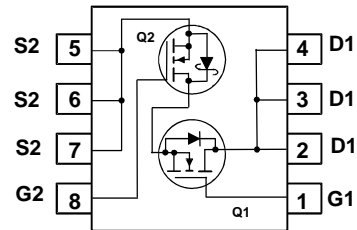


Top



Bottom

Power 56



### MOSFET Maximum Ratings $T_A = 25$ °C unless otherwise noted

Symbol	Parameter	Q1	Q2	Units
$V_{DS}$	Drain to Source Voltage	30	30	V
$V_{GS}$	Gate to Source Voltage (Note 3)	$\pm 20$	$\pm 20$	V
$I_D$	Drain Current -Continuous $T_C = 25$ °C	30	40	A
	-Continuous $T_A = 25$ °C	12 <sup>1a</sup>	22 <sup>1b</sup>	
	-Pulsed	40	60	
$P_D$	Power Dissipation for Single Operation $T_A = 25$ °C	2.2 <sup>1a</sup>	2.5 <sup>1b</sup>	W
	$T_A = 25$ °C	1.0 <sup>1c</sup>	1.0 <sup>1d</sup>	
$T_J, T_{STG}$	Operating and Storage Junction Temperature Range	-55 to +150		°C

### Thermal Characteristics

$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	57 <sup>1a</sup>	50 <sup>1b</sup>	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	125 <sup>1c</sup>	120 <sup>1d</sup>	
$R_{\theta JC}$	Thermal Resistance, Junction to Case	3.5	2	

### Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDMS7700S	FDMS7700S	Power 56	13 "	12 mm	3000 units

**Electrical Characteristics**  $T_J = 25\text{ }^\circ\text{C}$  unless otherwise noted

Symbol	Parameter	Test Conditions	Type	Min	Typ	Max	Units
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**Off Characteristics**

$BV_{DSS}$	Drain to Source Breakdown Voltage	$I_D = 250\text{ }\mu\text{A}$ , $V_{GS} = 0\text{ V}$ $I_D = 1\text{ mA}$ , $V_{GS} = 0\text{ V}$	Q1 Q2	30 30			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = 250\text{ }\mu\text{A}$ , referenced to $25\text{ }^\circ\text{C}$ $I_D = 1\text{ mA}$ , referenced to $25\text{ }^\circ\text{C}$	Q1 Q2		15 14		mV/ $^\circ\text{C}$
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = 24\text{ V}$ , $V_{GS} = 0\text{ V}$	Q1 Q2			1 500	$\mu\text{A}$ $\mu\text{A}$
$I_{GSS}$	Gate to Source Leakage Current	$V_{GS} = 20\text{ V}$ , $V_{DS} = 0\text{ V}$	Q1 Q2			100 100	nA nA

**On Characteristics**

$V_{GS(th)}$	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}$ , $I_D = 250\text{ }\mu\text{A}$ $V_{GS} = V_{DS}$ , $I_D = 1\text{ mA}$	Q1 Q2	1 1	1.8 1.5	3 3	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	$I_D = 250\text{ }\mu\text{A}$ , referenced to $25\text{ }^\circ\text{C}$ $I_D = 1\text{ mA}$ , referenced to $25\text{ }^\circ\text{C}$	Q1 Q2		-6 -4		mV/ $^\circ\text{C}$
$r_{DS(on)}$	Drain to Source On Resistance	$V_{GS} = 10\text{ V}$ , $I_D = 12\text{ A}$ $V_{GS} = 4.5\text{ V}$ , $I_D = 10\text{ A}$ $V_{GS} = 10\text{ V}$ , $I_D = 12\text{ A}$ , $T_J = 125\text{ }^\circ\text{C}$	Q1		6.0 8.5 8.3	7.5 12 12	m $\Omega$
		$V_{GS} = 10\text{ V}$ , $I_D = 20\text{ A}$ $V_{GS} = 4.5\text{ V}$ , $I_D = 18\text{ A}$ $V_{GS} = 10\text{ V}$ , $I_D = 20\text{ A}$ , $T_J = 125\text{ }^\circ\text{C}$	Q2		1.9 2.2 2.1	2.4 2.9 3.4	
$g_{FS}$	Forward Transconductance	$V_{DS} = 5\text{ V}$ , $I_D = 12\text{ A}$ $V_{DS} = 5\text{ V}$ , $I_D = 20\text{ A}$	Q1 Q2		63 160		S

**Dynamic Characteristics**

$C_{iss}$	Input Capacitance	Q1: $V_{DS} = 15\text{ V}$ , $V_{GS} = 0\text{ V}$ , $f = 1\text{ MHz}$	Q1 Q2		1315 7240	1750 9630	pF
$C_{oss}$	Output Capacitance	Q2: $V_{DS} = 15\text{ V}$ , $V_{GS} = 0\text{ V}$ , $f = 1\text{ MHz}$	Q1 Q2		445 2690	600 3580	pF
$C_{rss}$	Reverse Transfer Capacitance	$V_{DS} = 15\text{ V}$ , $V_{GS} = 0\text{ V}$ , $f = 1\text{ MHz}$	Q1 Q2		45 185	70 280	pF
$R_g$	Gate Resistance		Q1 Q2		0.9 0.8		$\Omega$

**Switching Characteristics**

$t_{d(on)}$	Turn-On Delay Time	Q1: $V_{DD} = 15\text{ V}$ , $I_D = 12\text{ A}$ , $R_{GEN} = 6\text{ }\Omega$	Q1 Q2		8.6 21	18 34	ns	
$t_r$	Rise Time		Q1 Q2		2.5 9.2	10 18	ns	
$t_{d(off)}$	Turn-Off Delay Time	Q2: $V_{DD} = 15\text{ V}$ , $I_D = 20\text{ A}$ , $R_{GEN} = 6\text{ }\Omega$	Q1 Q2		20 58	32 93	ns	
$t_f$	Fall Time		Q1 Q2		2.3 6.8	10 14	ns	
$Q_g$	Total Gate Charge	$V_{GS} = 0\text{ V}$ to $10\text{ V}$	Q1 $V_{DD} = 15\text{ V}$ , $I_D = 12\text{ A}$	Q1 Q2		20 105	28 147	nC
				Q1 Q2		9.3 48	13 67	nC
$Q_{gs}$	Gate to Source Gate Charge	Q2 $V_{DD} = 15\text{ V}$ , $I_D = 20\text{ A}$	Q1 Q2		4.3 19		nC	
$Q_{gd}$	Gate to Drain "Miller" Charge		Q1 Q2		2.2 11		nC	

### Electrical Characteristics $T_J = 25\text{ }^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Type	Min	Typ	Max	Units
<b>Drain-Source Diode Characteristics</b>							
$V_{SD}$	Source to Drain Diode Forward Voltage	$V_{GS} = 0\text{ V}, I_S = 12\text{ A}$ (Note 2)	Q1		0.8	1.2	V
		$V_{GS} = 0\text{ V}, I_S = 20\text{ A}$ (Note 2)	Q2		0.7	1.2	
$t_{rr}$	Reverse Recovery Time	$I_F = 12\text{ A}, di/dt = 100\text{ A}/\mu\text{s}$	Q1		27	43	ns
			Q2		53	85	
$Q_{rr}$	Reverse Recovery Charge	$I_F = 20\text{ A}, di/dt = 300\text{ A}/\mu\text{s}$	Q1		10	18	nC
			Q2		100	160	

**Notes:**

1:  $R_{\theta JA}$  is determined with the device mounted on a 1 in<sup>2</sup> pad 2 oz copper pad on a 1.5 x 1.5 in. board of FR-4 material.  $R_{\theta JC}$  is guaranteed by design while  $R_{\theta CA}$  is determined by the user's board design.



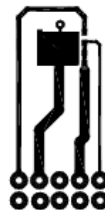
a. 57 °C/W when mounted on a 1 in<sup>2</sup> pad of 2 oz copper



b. 50 °C/W when mounted on a 1 in<sup>2</sup> pad of 2 oz copper



c. 125 °C/W when mounted on a minimum pad of 2 oz copper



d. 120 °C/W when mounted on a minimum pad of 2 oz copper

2: Pulse Test: Pulse Width < 300  $\mu\text{s}$ , Duty cycle < 2.0%.

3: As an N-ch device, the negative Vgs rating is for low duty cycle pulse occurrence only. No continuous rating is implied.

**Typical Characteristics (Q1 N-Channel)**  $T_J = 25^\circ\text{C}$  unless otherwise noted

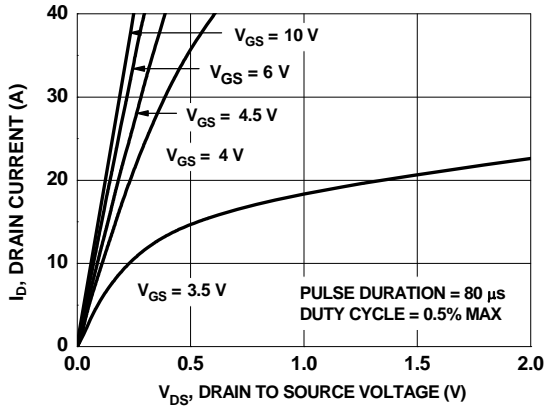


Figure 1. On Region Characteristics

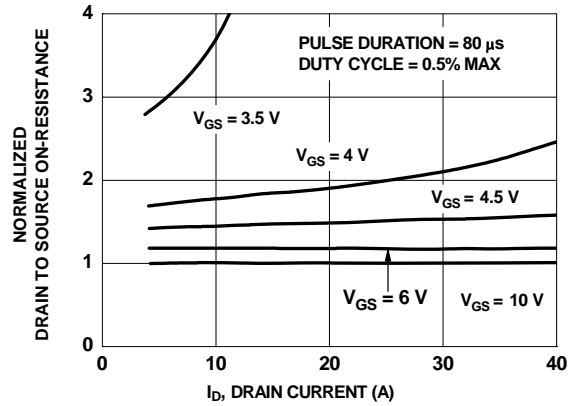


Figure 2. Normalized On-Resistance vs Drain Current and Gate Voltage

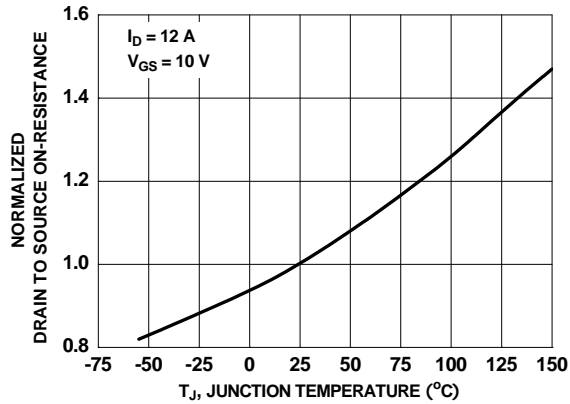


Figure 3. Normalized On Resistance vs Junction Temperature

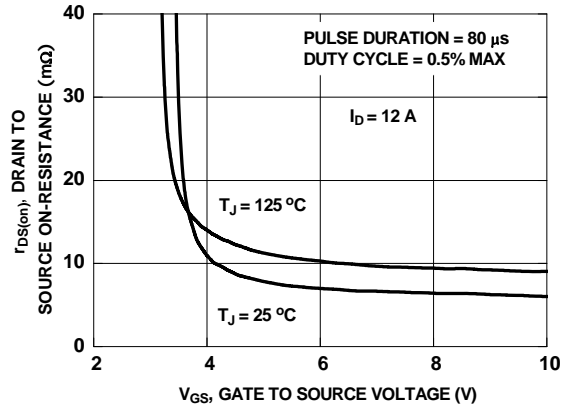


Figure 4. On-Resistance vs Gate to Source Voltage

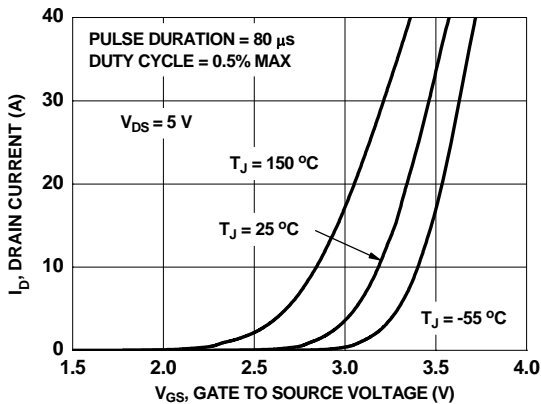


Figure 5. Transfer Characteristics

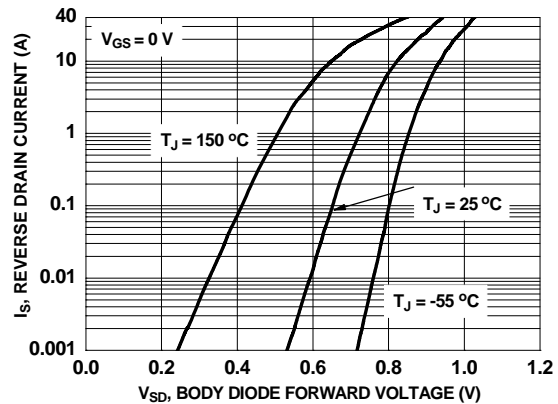
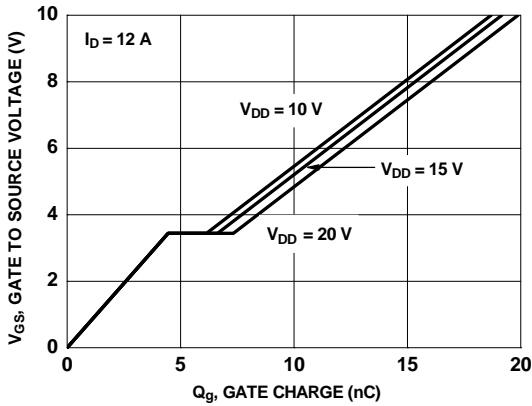
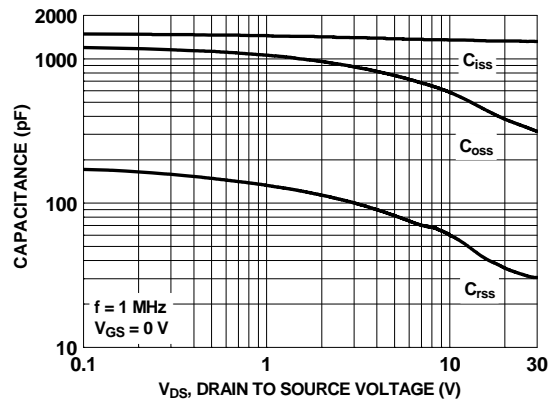


Figure 6. Source to Drain Diode Forward Voltage vs Source Current

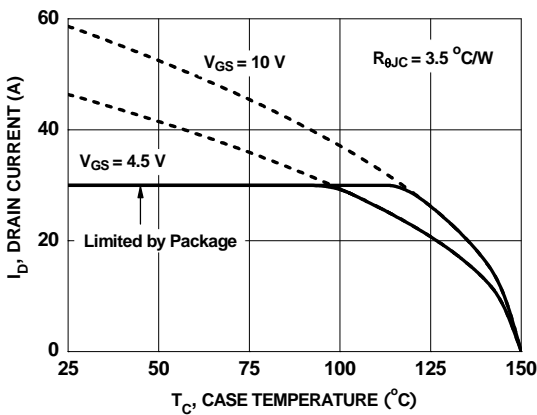
**Typical Characteristics (Q1 N-Channel)**  $T_J = 25^\circ\text{C}$  unless otherwise noted



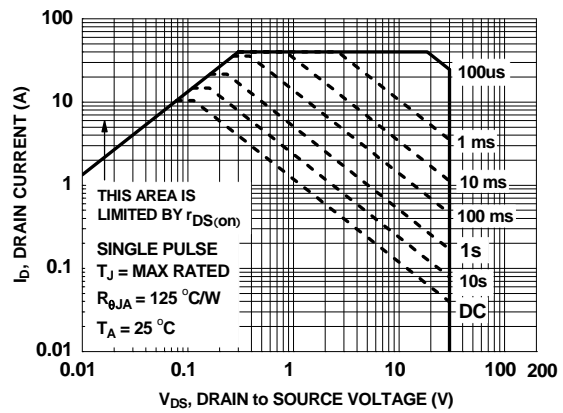
**Figure 7. Gate Charge Characteristics**



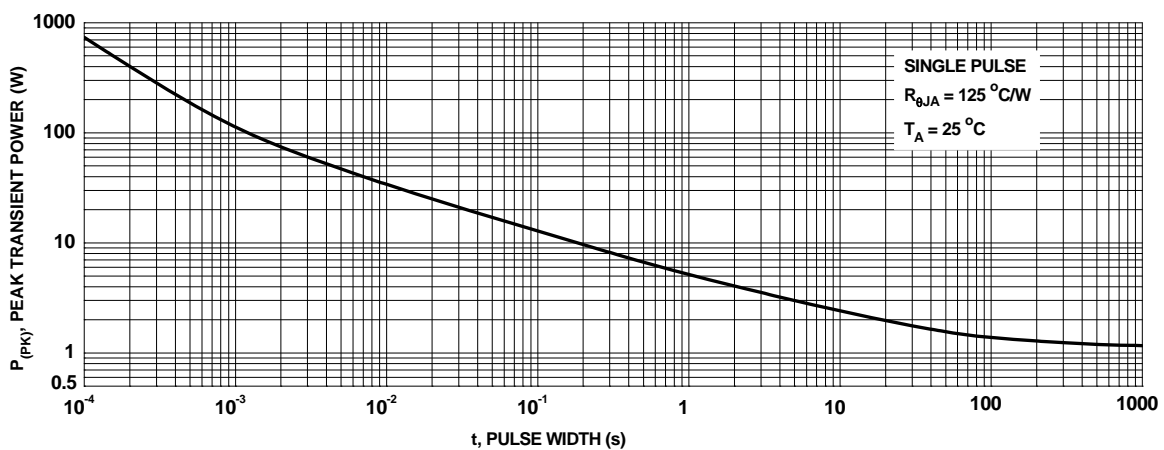
**Figure 8. Capacitance vs Drain to Source Voltage**



**Figure 9. Maximum Continuous Drain Current vs Case Temperature**

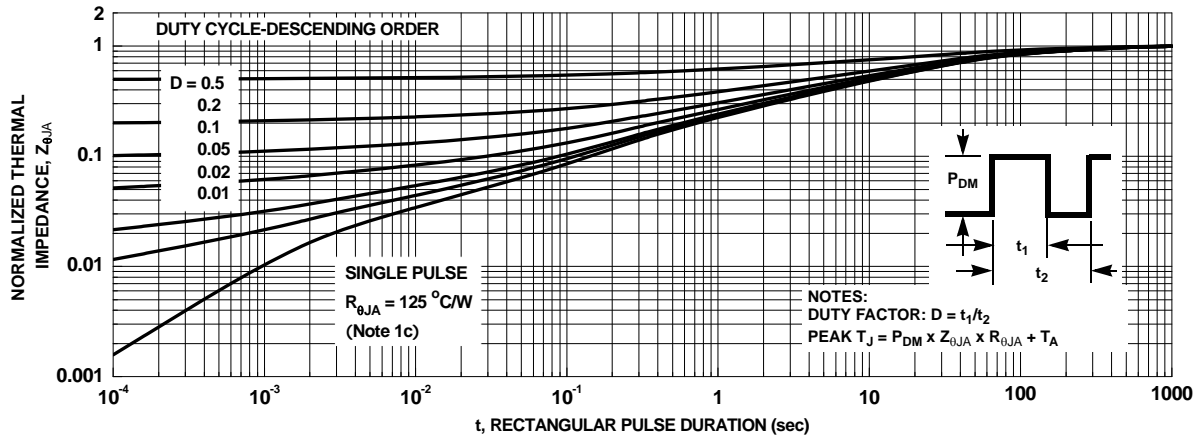


**Figure 10. Forward Bias Safe Operating Area**



**Figure 11. Single Pulse Maximum Power Dissipation**

**Typical Characteristics (Q1 N-Channel)**  $T_J = 25^\circ\text{C}$  unless otherwise noted



**Figure 12. Junction-to-Ambient Transient Thermal Response Curve**

### Typical Characteristics (Q2 SyncFET)

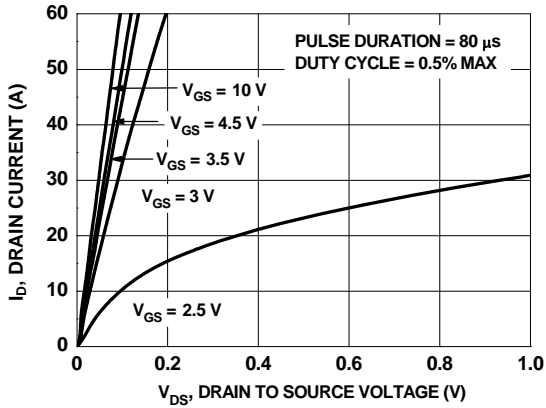


Figure 13. On-Region Characteristics

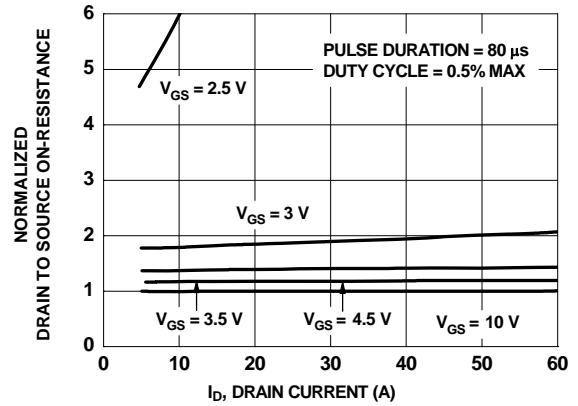


Figure 14. Normalized on-Resistance vs Drain Current and Gate Voltage

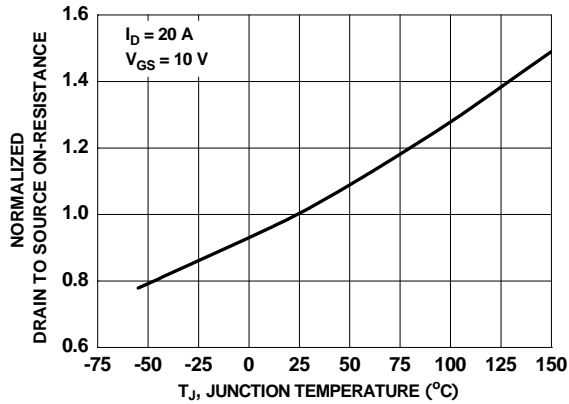


Figure 15. Normalized On-Resistance vs Junction Temperature

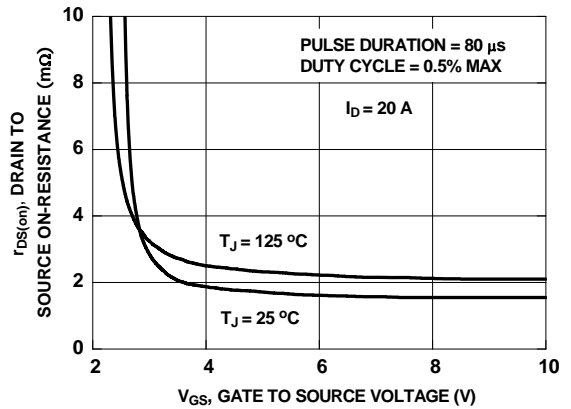


Figure 16. On-Resistance vs Gate to Source Voltage

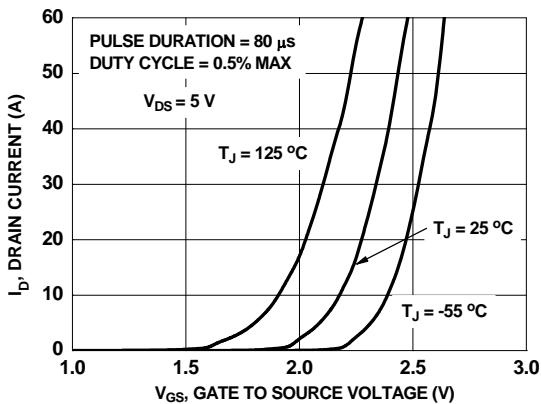


Figure 17. Transfer Characteristics

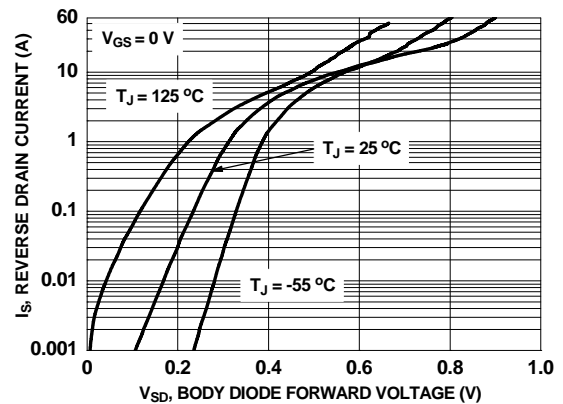


Figure 18. Source to Drain Diode Forward Voltage vs Source Current



### Typical Characteristics (Q2 SyncFET)

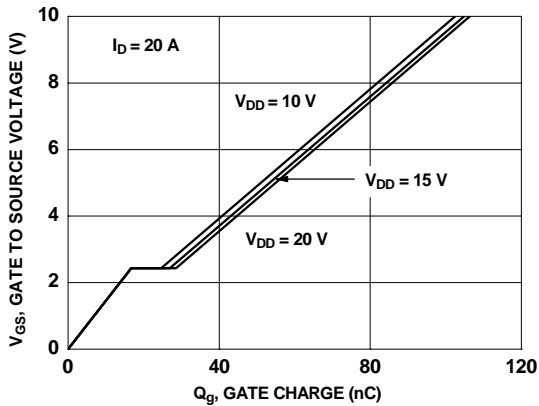


Figure 19. Gate Charge Characteristics

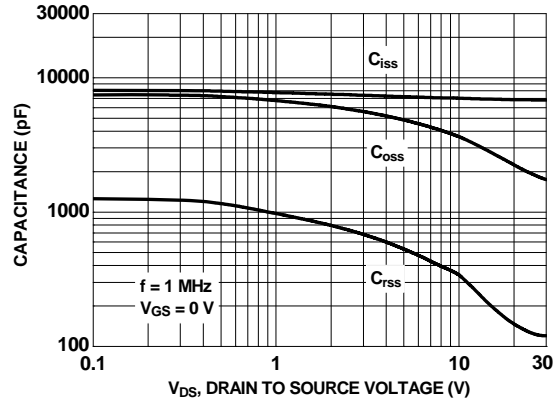


Figure 20. Capacitance vs Drain to Source Voltage

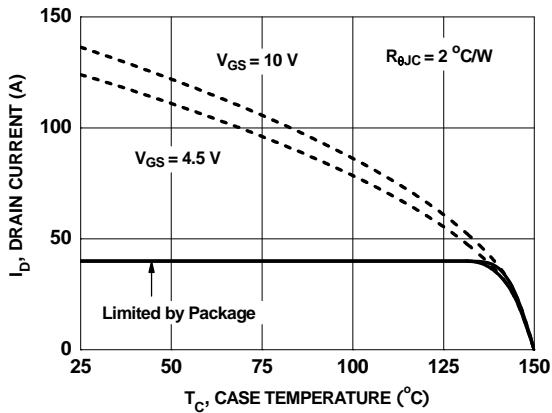


Figure 21. Maximum Continuous Drain Current vs Case Temperature

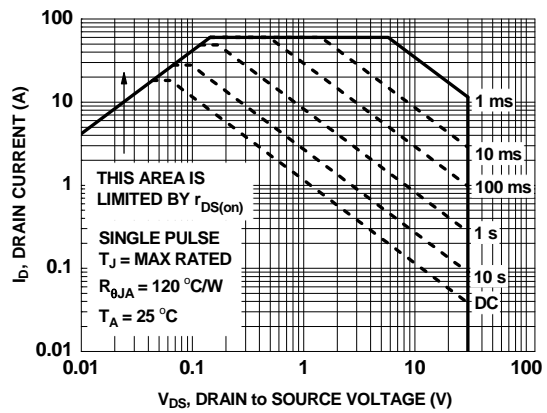


Figure 22. Forward Bias Safe Operating Area

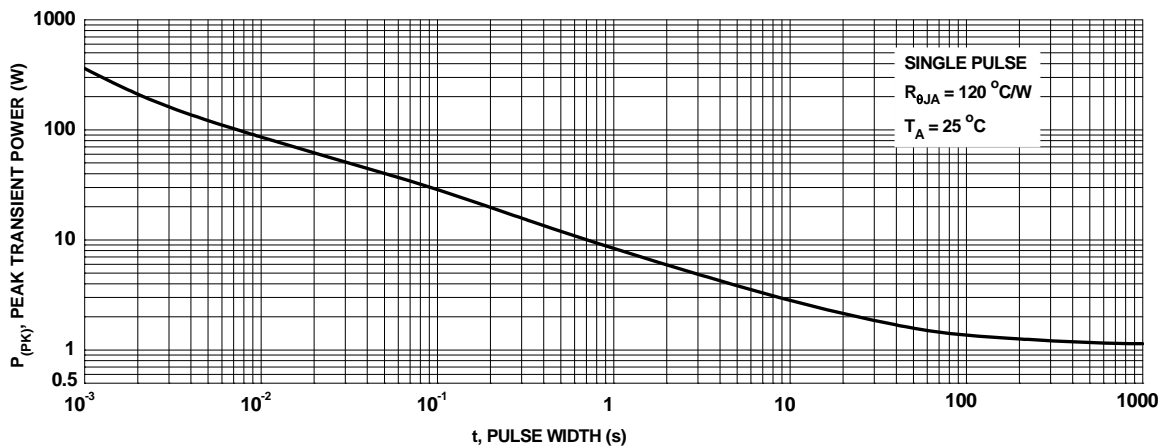


Figure 23. Single Pulse Maximum Power Dissipation

### Typical Characteristics (Q2 SyncFET)

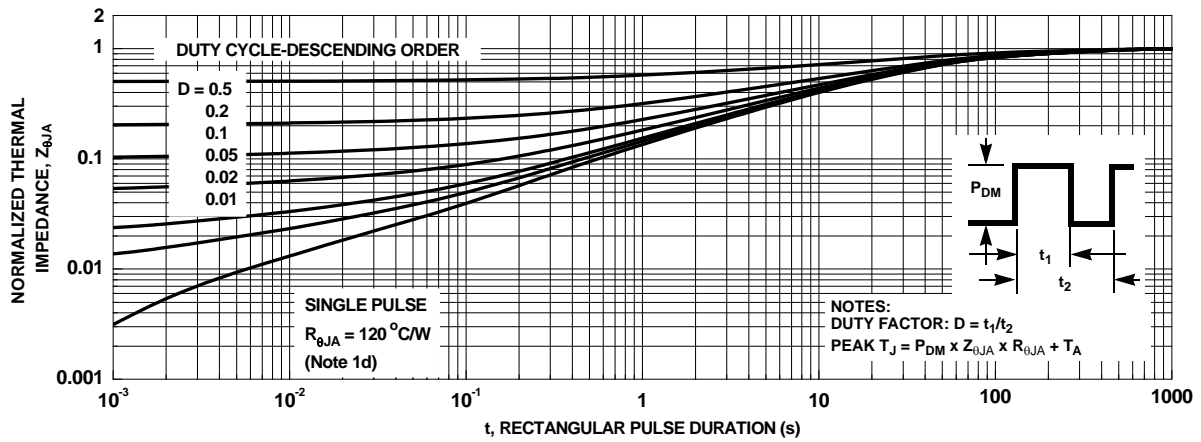


Figure 24. Junction-to-Ambient Transient Thermal Response Curve

## Typical Characteristics (continued)

### SyncFET<sup>™</sup> Schottky Body Diode Characteristics

Fairchild's SyncFET<sup>™</sup> process embeds a Schottky diode in parallel with PowerTrench<sup>®</sup> MOSFET. This diode exhibits similar characteristics to a discrete external Schottky diode in parallel with a MOSFET. Figure 25 shows the reverse recovery characteristic of the FDMS7700S.

Schottky barrier diodes exhibit significant leakage at high temperature and high reverse voltage. This will increase the power in the device.

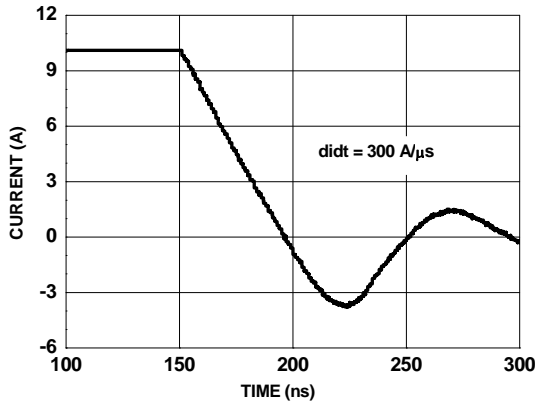


Figure 25. FDMS7700S SyncFET<sup>™</sup> Body Diode Reverse Recovery Characteristic

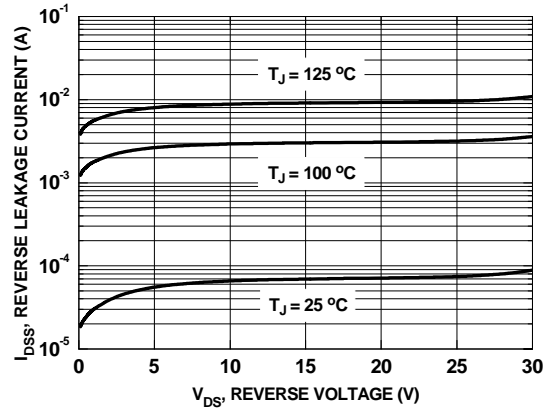


Figure 26. SyncFET<sup>™</sup> Body Diode Reverse Leakage vs. Drain-Source Voltage



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